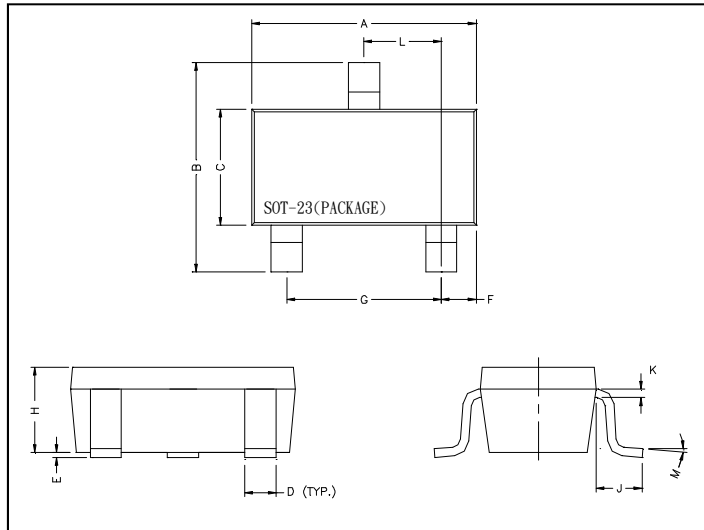
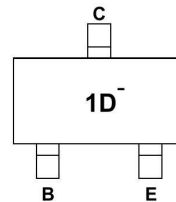


GMBTA42**NPN EPITAXIAL PLANAR TRANSISTOR****Description**

The GMBTA42 is designed for high voltage transistor.

Package Dimensions

Marking:



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	2.70	3.10	G	1.90	REF.
B	2.40	2.80	H	1.00	1.30
C	1.40	1.60	K	0.10	0.20
D	0.35	0.50	J	0.40	-
E	0	0.10	L	0.85	1.15
F	0.45	0.55	M	0°	10°

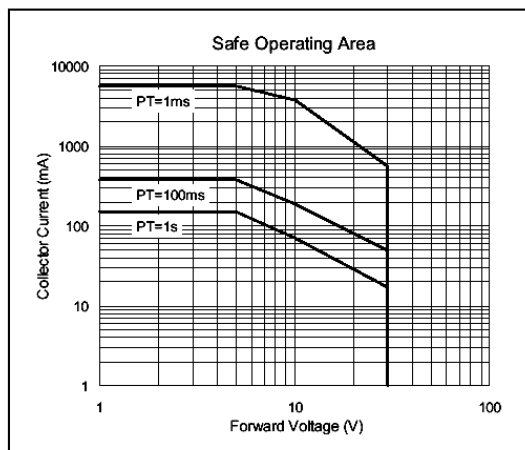
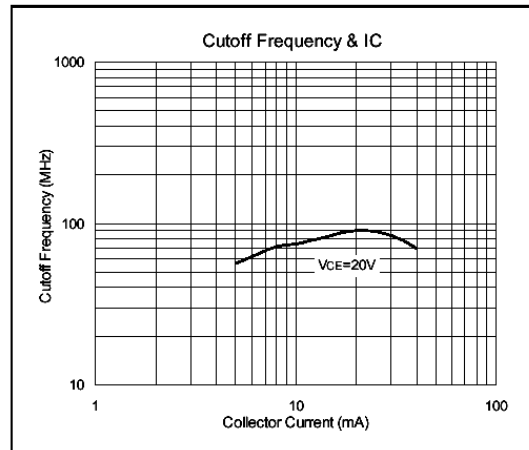
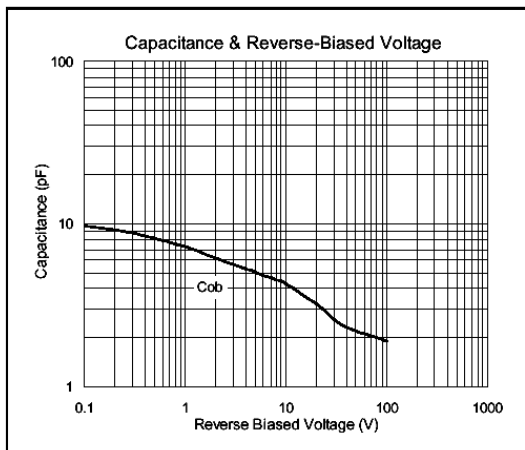
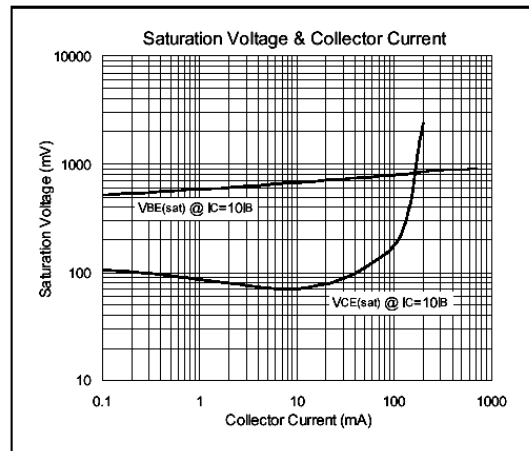
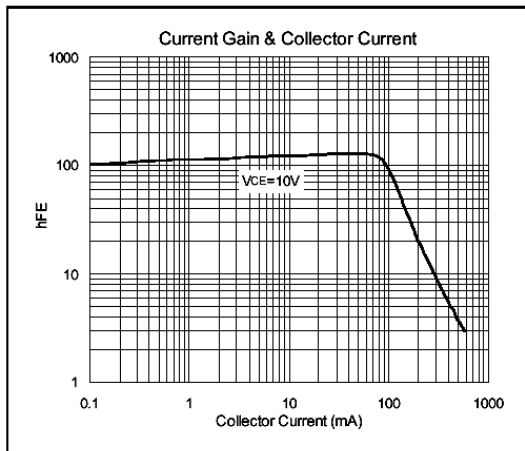
Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	°C
Storage Temperature	Tstg	-55~+150	°C
Collector to Base Voltage	VCBO	300	V
Collector to Emitter Voltage	VCEO	300	V
Emitter to Base Voltage	VEBO	6	V
Collector Current	IC	500	mA
Total Power Dissipation	PD	350	mW

Characteristics at Ta = 25°C

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	300	-	-	V	IC=100uA, IE=0
BVCEO	300	-	-	V	IC=1mA, IB=0
BVEBO	6	-	-	V	IE=100uA, IC=0
ICBO	-	-	100	nA	VCB=200V, IE=0
IEBO	-	-	100	nA	VEB=6V, IC=0
VCE(sat)	-	-	500	mV	IC=20mA, IB=2mA
VBE(sat)	-	-	900	mV	IC=20mA, IB=2mA
hFE1	25	-	-		VCE=10V, IC=1mA
hFE2	40	-	-		VCE=10V, IC=10mA
hFE3	40	-	-		VCE=10V, IC=30mA
fT	50	-	-	MHz	VCE=20V, IC=10mA, f=100MHz
Cob	-	-	3	pF	VCB=20V, f=1MHz

Characteristics Curve

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